PRODUCT NAME : 2N5551 NPN General Purpose Transistor (Pack of 5)

PRICE : Rs 29.00
SKU : RM2097

DESCRIPTION

Features

- Collector-Emitter Volt (Vceo): 160V
- Collector-Base Volt (Vcbo): 180V
- Collector Current (Ic): 0.6A
- hfe: 80-250 @ 10mA
- Power Dissipation (Ptot): 625mW
- Current-Gain-Bandwidth (ftotal): 300MHz
- Type: NPN

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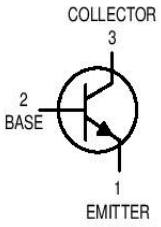
SEMICONDUCTOR TECHNICAL DATA

Order this document
by 2N5550/D

Amplifier Transistors
NPN Silicon

2N5550
2N5551*

*Motorola Preferred Device



CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	2N5550	2N5551	Unit
Collector–Emitter Voltage	V_{CEO}	140	160	Vdc
Collector–Base Voltage	V_{CBO}	160	180	Vdc
Emitter–Base Voltage	V_{EBO}	6.0		Vdc
Collector Current — Continuous	I_C	600		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	 2N5550 2N5551	$V_{(BR)CEO}$	 140 160	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 2N5550 2N5551	$V_{(BR)CBO}$	 160 180	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 120 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_A = 100°C) (V_{CB} = 120 Vdc, I_E = 0, T_A = 100°C)	 2N5550 2N5551 2N5550 2N5551	I_{CBO}	 — — — —	 100 50 100 50	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = 4.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS(1)					
DC Current Gain		h_{FE}			—
(I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc)	2N5550		60	—	
	2N5551		80	—	
(I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	2N5550		60	250	
	2N5551		80	250	
(I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	2N5550		20	—	
	2N5551		30	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	Both Types		—	0.15	
(I_C = 50 mAdc, I_B = 5.0 mAdc)	2N5550		—	0.25	
	2N5551		—	0.20	
Base–Emitter Saturation Voltage		$V_{BE(sat)}$			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	Both Types		—	1.0	
(I_C = 50 mAdc, I_B = 5.0 mAdc)	2N5550		—	1.2	
	2N5551		—	1.0	
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	100	300	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	—	6.0	pF
Input Capacitance		C_{ibo}			pF
(V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)	2N5550		—	30	
	2N5551		—	20	
Small–Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)		h_{fe}	50	200	—
Noise Figure		NF			dB
(I_C = 250 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ,	2N5550		—	10	
f = 1.0 kHz)	2N5551		—	8.0	

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.